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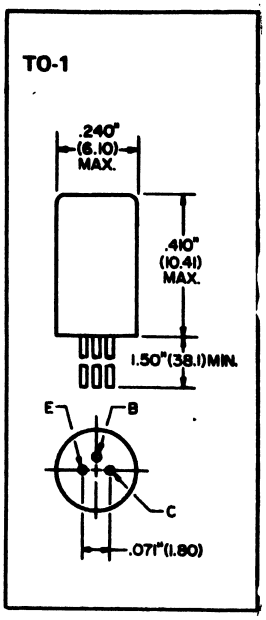
2N200
P-N-P GERMANIUM TRANSISTOR

*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-Base Voltage	25 v
Emitter-Base Voltage	25 v
Collector Current	300 ma
Total Device Dissipation at (or below) 25°C	150 mw
Operating Collector Junction Temperature	85°C
Storage Temperature Range	−65°C to 100°C

Transistor Outline



electrical characteristics at 25°C free-air temperature

PARAMETER		TEST CONDITIONS	2N200 MIN	2N200 TYP	2N200 MAX	UNIT
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\ \mu a$, $I_E = 0$	25			v
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\ \mu a$, $I_C = 0$	25			v
*V_{PT}	Punch Through Voltage†	$V_{EBfl} = 1$ v	25			v
*I_{CBO}	Collector Cutoff Current	$V_{CB} = 25$ v, $I_E = 0$		3	50	μa
*I_{EBO}	Emitter Cutoff Current	$V_{EB} = 25$ v, $I_C = 0$		2	50	μa
*h_{FE}	Static Forward Current Transfer Ratio	$V_{CE} = 1$ v, $I_C = 10$ ma	20	100		
		$V_{CE} = 0.35$ v, $I_C = 200$ ma	10	100		
*V_{BE}	Base-Emitter Voltage	$I_B = 0.5$ ma, $I_C = 10$ ma	0.15	0.22	0.40	v
*$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_B = 0.5$ ma, $I_C = 10$ ma		0.07	0.20	v
		$I_B = 0.25$ ma, $I_C = 10$ ma				v
		$I_B = 0.17$ ma, $I_C = 10$ ma				v
		$I_B = 0.13$ ma, $I_C = 10$ ma				v